High Current Transistors

NPN Silicon

MAXIMUM RATINGS

Rating	Symbol	BC635	BC637	BC639	Unit
Collector-Emitter Voltage	V _{CEO}	45	60	80	Vdc
Collector-Base Voltage	V _{CBO}	45	60	80	Vdc
Emitter-Base Voltage	V _{EBO}	5.0			Vdc
Collector Current — Continuous	I _C	0.5			Adc
Total Device Dissipation @ T _A = 25°C Derate above 25°C	P _D	625 5.0			mW mW/°C
Total Device Dissipation @ T _C = 25°C Derate above 25°C	P _D	1.5 12		Watt mW/°C	
Operating and Storage Junction Temperature Range	T _J , T _{stg}	-55 to +150		°C	
Electrostatic Discharge	ESD	HBM>16000, MM>2000		V	

THERMAL CHARACTERISTICS

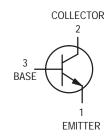
Characteristic	Symbol	Max	Unit
Thermal Resistance, Junction to Ambient	$R_{ heta JA}$	200	°C/W
Thermal Resistance, Junction to Case	$R_{\theta JC}$	83.3	°C/W



ON Semiconductor

Formerly a Division of Motorola

http://onsemi.com





TO-92 (TO-226AA) CASE 29 STYLE 14

ORDERING INFORMATION

Device Package		Shipping		
BC635RL1	TO-92	2000 Units/Tape & Reel		
BC635ZL1	TO-92	2000 Units/Ammo Pack		
BC637	TO-92	5000 Units/Box		
BC639	TO-92	5000 Units/Box		
BC639RL1	TO-92	2000 Units/Tape & Reel		
BC639ZL1	TO-92	2000 Units/Ammo Pack		

ELECTRICAL CHARACTERISTICS (T_A = 25°C unless otherwise noted)

Characteristic		Symbol	Min	Тур	Max	Unit
OFF CHARACTERISTICS		•	•		•	
Collector-Emitter Breakdown Voltage ⁽¹⁾ (I _C = 10 mAdc, I _B = 0)	BC635 BC637 BC639	V _(BR) CEO	45 60 80	_ _ _	_ _ _	Vdc
Collector-Base Breakdown Voltage ($I_C = 100 \mu Adc$, $I_E = 0$)	BC635 BC637 BC639	V _(BR) CBO	45 60 80	_ _ _	_ _ _	Vdc
Emitter-Base Breakdown Voltage $(I_E = 10 \mu Adc, I_C = 0)$		V _{(BR)EBO}	5.0	_	_	Vdc
Collector Cutoff Current $(V_{CB} = 30 \text{ Vdc}, I_E = 0)$ $(V_{CB} = 30 \text{ Vdc}, I_E = 0, T_A = 125^{\circ}\text{C})$		Ісво		_ _ _	100 10	nAdc μAdc
ON CHARACTERISTICS ⁽¹⁾		•				•
DC Current Gain $ (I_C = 5.0 \text{ mAdc}, V_{CE} = 2.0 \text{ Vdc}) $ $ (I_C = 150 \text{ mAdc}, V_{CE} = 2.0 \text{ Vdc}) $ $ (I_C = 500 \text{ mA}, V_{CE} = 2.0 \text{ V}) $	BC635 BC637 BC639	h _{FE}	25 40 40 40 40 25		 250 160 160 	_
Collector-Emitter Saturation Voltage (I _C = 500 mAdc, I _B = 50 mAdc)		V _{CE(sat)}	_	_	0.5	Vdc
Base–Emitter On Voltage (I _C = 500 mAdc, V _{CE} = 2.0 Vdc)		V _{BE(on)}	_	_	1.0	Vdc
DYNAMIC CHARACTERISTICS		•	•		•	•
Current-Gain — Bandwidth Product (I _C = 50 mAdc, V _{CE} = 2.0 Vdc, f = 100 MHz)		f _T		200	_	MHz
Output Capacitance (V _{CB} = 10 Vdc, I _E = 0, f = 1.0 MHz)		C _{ob}		7.0	_	pF
Input Capacitance (V _{EB} = 0.5 Vdc, I _C = 0, f = 1.0 MHz)		C _{ib}	_	50	_	pF

^{1.} Pulse Test: Pulse Width ≤ 300 μs, Duty Cycle 2.0%.

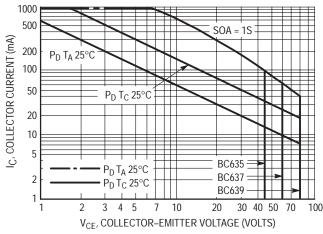


Figure 1. Active Region Safe Operating Area

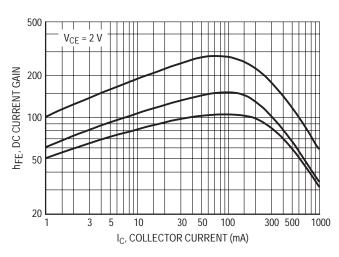


Figure 2. DC Current Gain

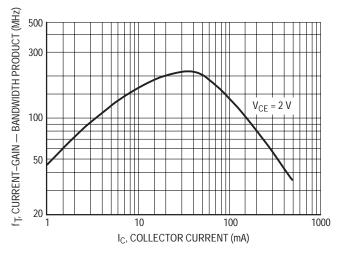


Figure 3. Current-Gain — Bandwidth Product

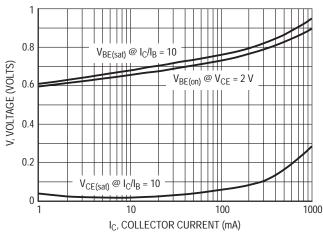


Figure 4. "Saturation" and "On" Voltages

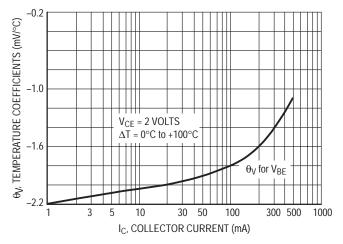
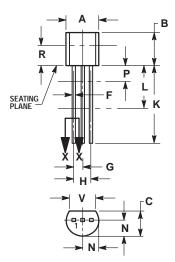


Figure 5. Temperature Coefficients

PACKAGE DIMENSIONS

TO-92 (TO-226AA) CASE 029-04 **ISSUE AD**



STYLF 14: PIN 1. EMITTER COLLECTOR BASE



- NOTES:
 1. DIMENSIONING AND TOLERANCING PER ANSI Y14.5M, 1982. CONTROLLING DIMENSION: INCH.
- CONTOUR OF PACKAGE BEYOND DIMENSION R
 IS UNCONTROLLED.
- DIMENSION F APPLIES BETWEEN P AND L DIMENSION D AND J APPLY BETWEEN L AND K MINIMUM. LEAD DIMENSION IS UNCONTROLLED IN P AND BEYOND DIMENSION K MINIMUM.

	INCHES		MILLIMETERS		
DIM	MIN	MAX	MIN MAX		
Α	0.175	0.205	4.45	5.20	
В	0.170	0.210	4.32	5.33	
С	0.125	0.165	3.18	4.19	
D	0.016	0.022	0.41	0.55	
F	0.016	0.019	0.41	0.48	
G	0.045	0.055	1.15	1.39	
Н	0.095	0.105	2.42	2.66	
J	0.015	0.020	0.39	0.50	
K	0.500		12.70		
L	0.250		6.35		
N	0.080	0.105	2.04	2.66	
Р		0.100		2.54	
R	0.115		2.93		
V	0.135		3.43		

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